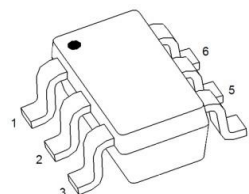


Dual Transistor (NPN+NPN)

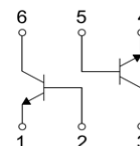
FEATURES

- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching



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MARKING: K2X



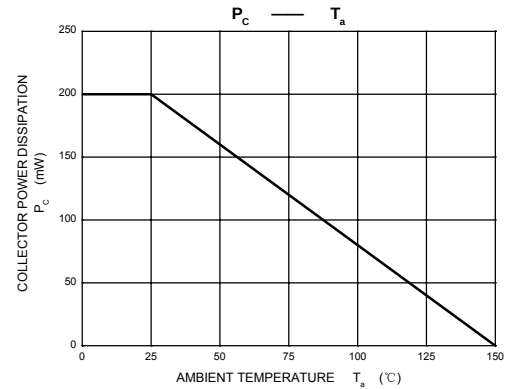
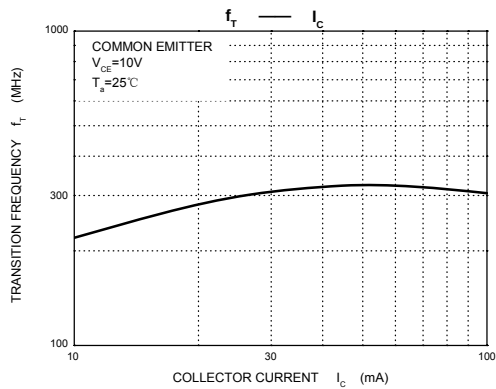
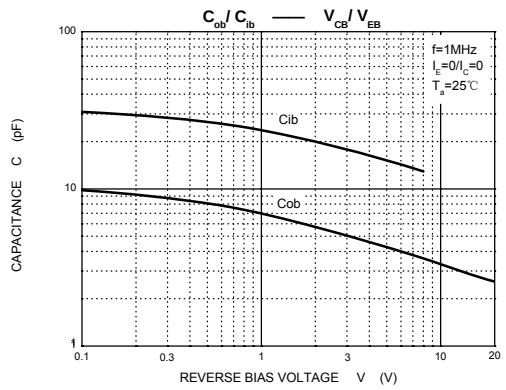
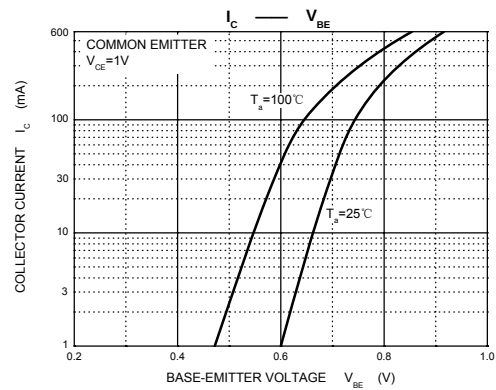
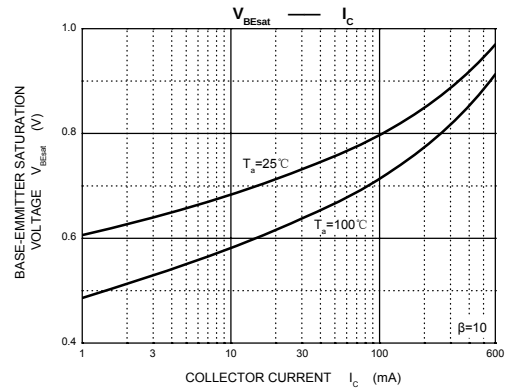
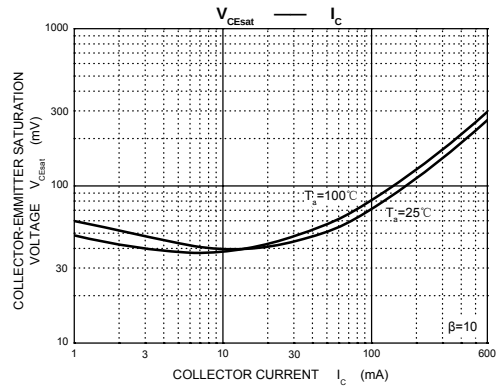
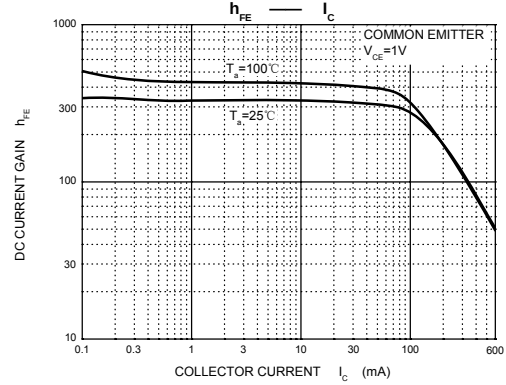
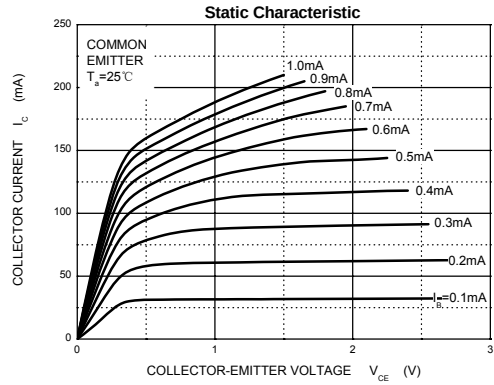
MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	0.6	A
P_C	Collector Power Dissipation	0.2	W
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	625	$^{\circ}\text{C/W}$
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55 to +150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

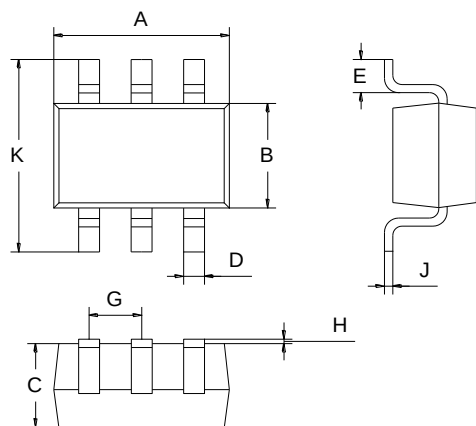
Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100 \mu A, I_E = 0$	60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1mA, I_B = 0$	40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100 \mu A, I_C = 0$	6		V
Collector cut-off current	I_{CBO}	$V_{CB} = 50V, I_E = 0$		0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = 35V, I_B = 0$		0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5V, I_C = 0$		0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = 1V, I_C = 0.1mA$	20		
	$h_{FE(2)}$	$V_{CE} = 1V, I_C = 1mA$	40		
	$h_{FE(3)}$	$V_{CE} = 1V, I_C = 10mA$	80		
	$h_{FE(4)}$	$V_{CE} = 1V, I_C = 150mA$	100	300	
	$h_{FE(5)}$	$V_{CE} = 2V, I_C = 500mA$	40		
Collector-emitter saturation voltage	$V_{CE(sat)1}$	$I_C = 150mA, I_B = 15mA$		0.4	V
	$V_{CE(sat)2}$	$I_C = 500mA, I_B = 50mA$		0.75	V
Base-emitter saturation voltage	$V_{BE(sat)1}$	$I_C = 150mA, I_B = 15mA$	0.75	0.95	V
	$V_{BE(sat)2}$	$I_C = 500mA, I_B = 50mA$		1.2	V
Transition frequency	f_T	$V_{CE} = 10V, I_C = 20mA, f = 100MHz$	250		MHz
Output capacitance	C_{ob}	$V_{CB} = 5V, I_E = 0, f = 1MHz$		6.5	pF
Delay time	t_d	$V_{CC} = 30V,$		15	nS
Rise time	t_r	$V_{BE} = 2V, I_C = 150mA, I_{B1} = 15mA$		20	nS
Storage time	t_s	$V_{CC} = 30V, I_C = 150mA, I_{B1} = -I_{B2} = 15mA$		225	nS
Fall time	t_f			30	nS

Typical Characteristics



Plastic surface mounted package

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Dimension	Min.	Max.
A	2.00	2.20
B	1.15	1.35
C	0.85	1.05
D	0.15	0.35
E	0.25	0.40
G	0.60	0.70
H	0.02	0.10
J	0.05	0.15
K	2.20	2.40

SOLDERING FOOTPRINT

